Preferred Device

Small Signal MOSFET 200 mAmps, 60 Volts

N-Channel TO-92

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current - Continuous - Pulsed	I _D	200 500	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	TL	300	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

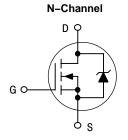


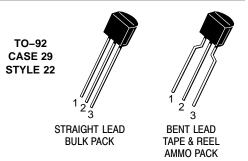
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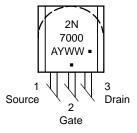
200 mAMPS 60 VOLTS

 $R_{DS(on)} = 5 \Omega$





MARKING DIAGRAM AND PIN ASSIGNMENT



A = Assembly Location

Y = Year WW = Work Week • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N7000

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS	OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage	e $(V_{GS} = 0, I_D = 10 \mu Adc)$	V _{(BR)DSS}	60	_	Vdc
Zero Gate Voltage Drain Current	I _{DSS}	- -	1.0 1.0	μAdc mAdc	
Gate-Body Leakage Current, Fo	rward $(V_{GSF} = 15 \text{ Vdc}, V_{DS} = 0)$	I _{GSSF}	-	-10	nAdc
ON CHARACTERISTICS (Note 1)				
Gate Threshold Voltage	$(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	V _{GS(th)}	0.8	3.0	Vdc
Static Drain-Source On-Resistar	nce $(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$	r _{DS(on)}		5.0 6.0	Ω
Drain-Source On-Voltage	$(V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc})$ $(V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc})$	V _{DS(on)}	_ _	2.5 0.45	Vdc
On–State Drain Current $(V_{GS} = 4.5 \text{ Vdc}, V_{DS} = 10 \text{ Vdc})$		I _{d(on)}	75	_	mAdc
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 200 mAdc)		9fs	100	_	μmhos
DYNAMIC CHARACTERISTICS	DYNAMIC CHARACTERISTICS				
Input Capacitance		C _{iss}	_	60	pF
Output Capacitance	$(V_{DS} = 25 \text{ V}, V_{GS} = 0, \\ f = 1.0 \text{ MHz})$	Coss	_	25	
Reverse Transfer Capacitance	1 – 110 1111 12)	C _{rss}	_	5.0	
SWITCHING CHARACTERISTICS (Note 1)				•	
Turn-On Delay Time	(V _{DD} = 15 V, I _D = 500 mA,	t _{on}	_	10	ns
Turn-Off Delay Time	$R_G = 25 \Omega$, $R_L = 30 \Omega$, $V_{gen} = 10 V$)	t _{off}	_	10	

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7000	TO-92	1000 Units / Bulk
2N7000G	TO-92 (Pb-Free)	1000 Units / Bulk
2N7000RLRA	TO-92	2000 Tape & Reel
2N7000RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel
2N7000RLRM	TO-92	2000 Tape & Ammo Box
2N7000RLRMG	TO-92 (Pb-Free)	2000 Tape & Ammo Box
2N7000RLRP	TO-92	2000 Tape & Ammo Box
2N7000RLRPG	TO-92 (Pb-Free)	2000 Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2N7000

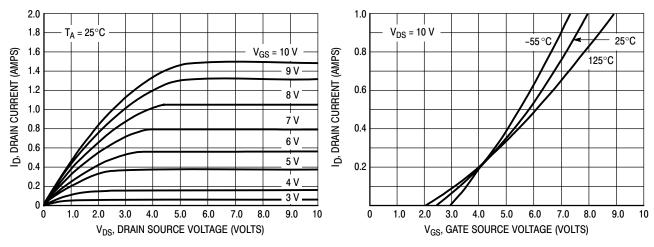


Figure 1. Ohmic Region

Figure 2. Transfer Characteristics

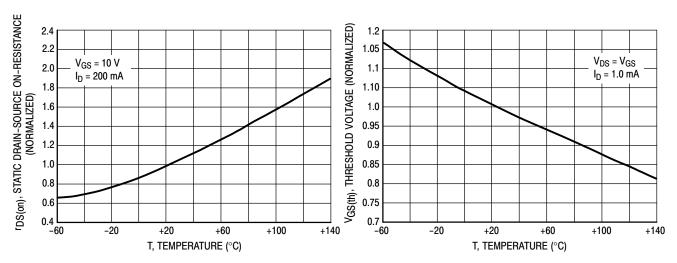


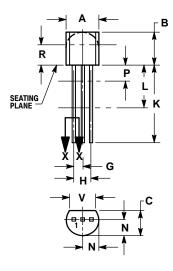
Figure 3. Temperature versus Static Drain-Source On-Resistance

Figure 4. Temperature versus Gate Threshold Voltage

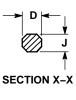
2N7000

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**

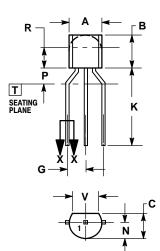


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р	-	0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
C	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 22:

PIN 1. SOURCE 2.

GATE

DRAIN

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